

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

## 2SC4738FT

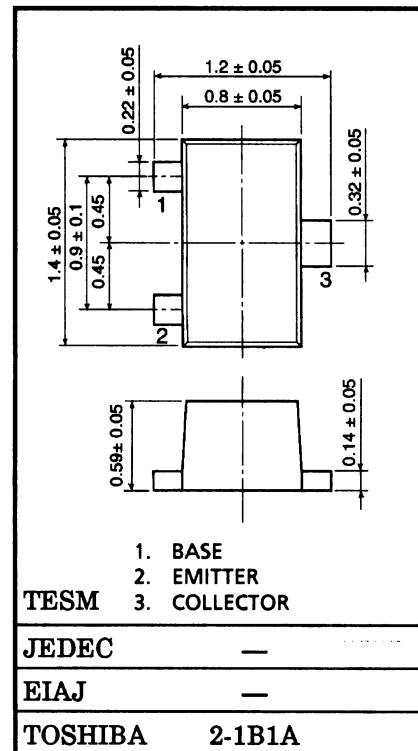
### Audio Frequency General Purpose Amplifier Applications

- High Voltage:  $V_{CE0} = 50\text{ V}$
- High Current:  $I_C = 150\text{ mA (max)}$
- High  $h_{FE}$ :  $h_{FE} = 120\text{ to }400$
- Excellent  $h_{FE}$  Linearity:  $h_{FE}(I_C = 0.1\text{ mA})/h_{FE}(I_C = 2\text{ mA}) = 0.95\text{ (typ.)}$
- Complementary to 2SA1832FT

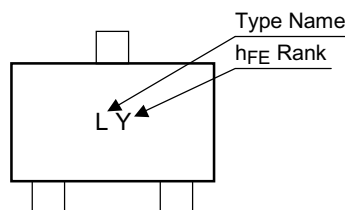
### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	150	mA
Base current	$I_B$	30	mA
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to 125	$^\circ\text{C}$

Unit in mm



### Marking



000630EAA1

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## Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = 60\text{ V}, I_E = 0$	—	—	0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	$\mu\text{A}$
DC current gain	$h_{FE}$ (Note)	$V_{CE} = 6\text{ V}, I_C = 2\text{ mA}$	120	—	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\text{ mA}, I_B = 10\text{ mA}$		0.1	0.25	V
Transition frequency	$f_T$	$V_{CE} = 10\text{ V}, I_C = 1\text{ mA}$	80	—	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	2.0	3.5	pF

Note:  $h_{FE}$  Classification Y (Y): 120 to 240, GR (G): 200 to 400

( ) Marking symbol

